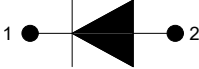


200mW SOD-323 Plastic-Encapsulate Zener Diode

1. Features

- Planar die construction
- 200mW power dissipation on ceramic PBC
- General purpose, medium current
- Ideally suited for automated assembly processes
- Available in lead free version

2. Marking and Circuit

Marking	Circuit
	

3. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameters	Symbol	Value	Unit
Forward voltage (Note 2) @I _F =10mA	V _F	0.9	V
Power dissipation (Note 1)	P _D	200	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage temperature range	T _{STG}	-55~+150	°C

1) Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm².

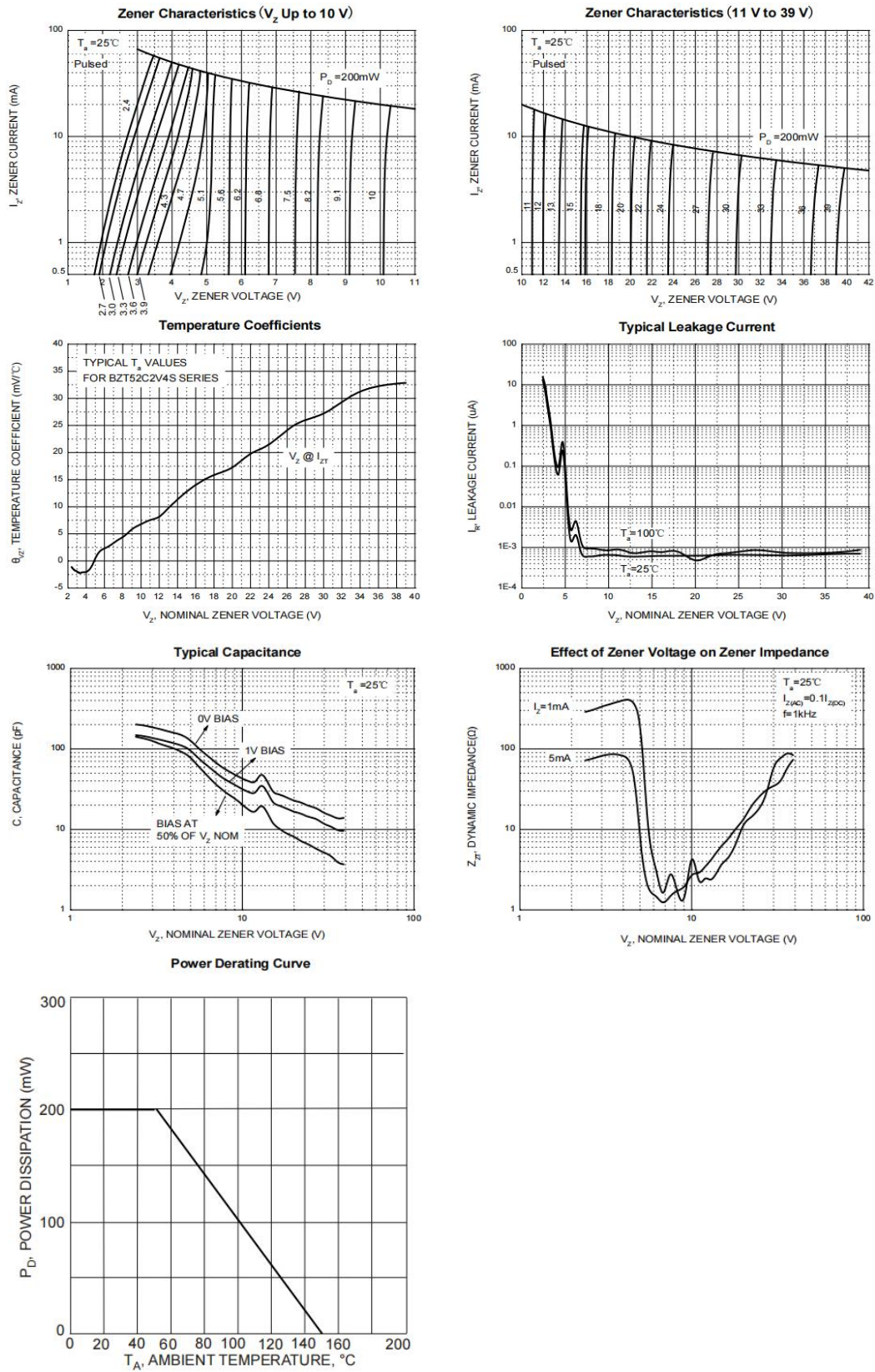
2) Short duration test pulse used to minimize self-heating effect.

3) f=1KHz.

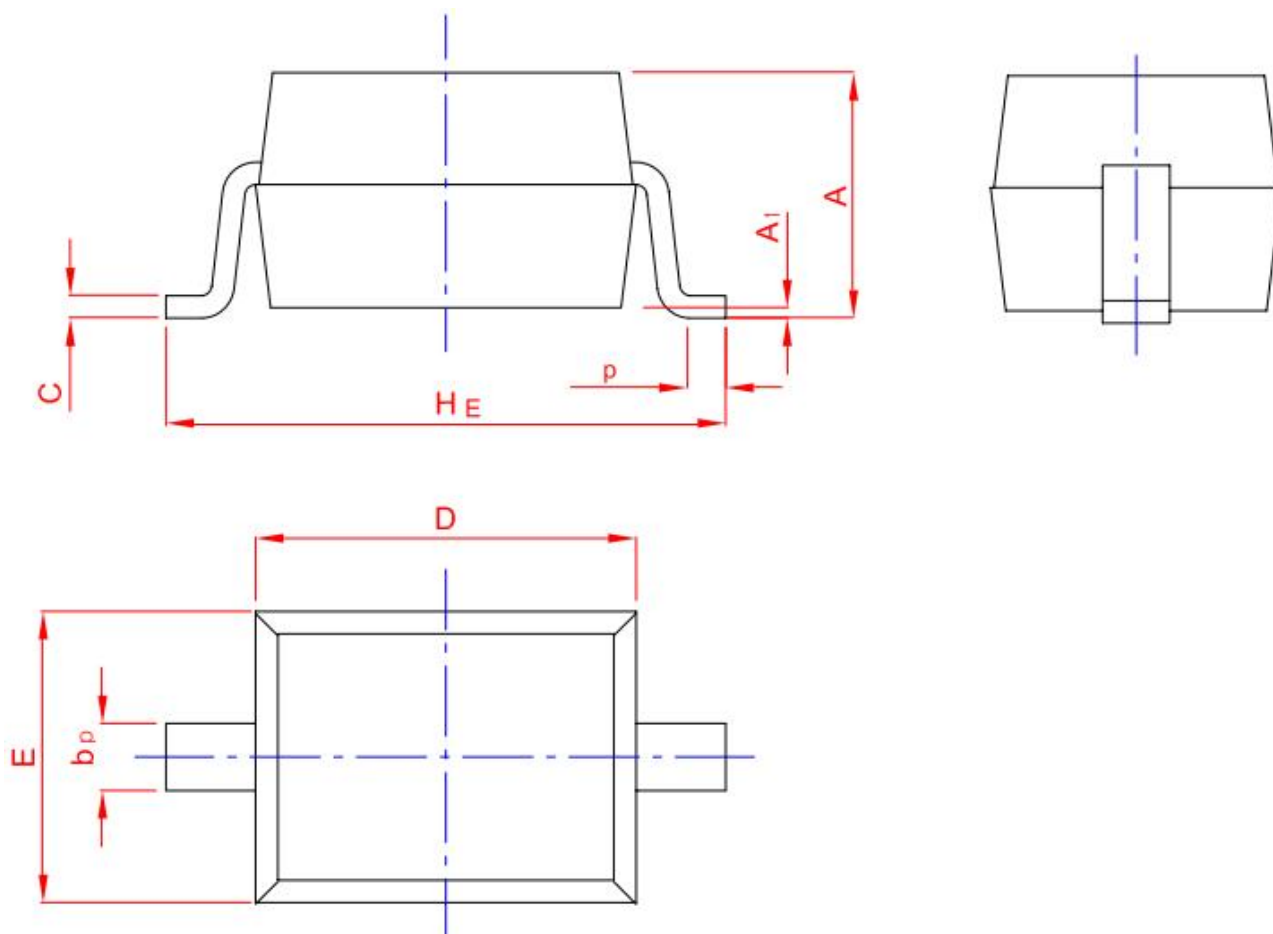
Electrical Characteristics (At TA = 25°C unless otherwise specified)

Device	Marking	Zener Voltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current (Note 2)		Typical Temperature coefficient @IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR	Min	Max	
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	uA	V			
BZT52C2V4S	WX	2.4	2.2	2.6	5	100	600	1.0	50.0	1.0	-3.5	0.0	5
BZT52C2V7S	W1	2.7	2.5	2.9	5	100	600	1.0	20.0	1.0	-3.5	0.0	5
BZT52C3V0S	W2	3.0	2.8	3.2	5	95	600	1.0	10.0	1.0	-3.5	0.0	5
BZT52C3V3S	W3	3.3	3.1	3.5	5	95	600	1.0	5.0	1.0	-3.5	0.0	5
BZT52C3V6S	W4	3.6	3.4	3.8	5	90	600	1.0	5.0	1.0	-3.5	0.0	5
BZT52C3V9S	W5	3.9	3.7	4.1	5	90	600	1.0	3.0	1.0	-3.5	0.0	5
BZT52C4V3S	W6	4.3	4.0	4.6	5	90	600	1.0	3.0	1.0	-3.5	0.0	5
BZT52C4V7S	W7	4.7	4.4	5.0	5	80	500	1.0	3.0	2.0	-3.5	0.2	5
BZT52C5V1S	W8	5.1	4.8	5.4	5	60	480	1.0	2.0	2.0	-2.7	1.2	5
BZT52C5V6S	W9	5.6	5.2	6.0	5	40	400	1.0	1.0	2.0	-2.0	2.5	5
BZT52C6V2S	WA	6.2	5.8	6.6	5	10	150	1.0	3.0	4.0	0.4	3.7	5
BZT52C6V8S	WB	6.8	6.4	7.2	5	15	80	1.0	2.0	4.0	1.2	4.5	5
BZT52C7V5S	WC	7.5	7.0	7.9	5	15	80	1.0	1.0	5.0	2.5	5.3	5
BZT52C8V2S	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1S	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10S	WF	10.0	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52C11S	WG	11.0	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12S	WH	12.0	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13S	WI	13.0	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15S	WJ	15.0	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52C16S	WK	16.0	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52C18S	WL	18.0	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52C20S	WM	20.0	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52C22S	WN	22.0	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52C24S	WO	24.0	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52C27S	WP	27.0	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30S	WQ	30.0	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33S	WR	33.0	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36S	WS	36.0	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39S	WT	39.0	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C43S	WU	43.0	40.0	46.0	2	130	250	0.5	0.1	33			2
BZT52C47S	WV	47.0	44.0	50.0	2	150	300	0.5	0.1	36			2
BZT52C51S	WW	51.0	48.0	54.0	2	170	300	0.5	0.1	39			2
BZT52C56S	X1	56.0	52.0	60.0	2	170	325	0.5	0.1	43			2
BZT52C62S	X2	62.0	58.0	66.0	2	190	350	0.5	0.1	47			2
BZT52C68S	X3	68.0	64.0	72.0	2	190	350	0.5	0.1	52			2
BZT52C75S	X4	75.0	70.0	79.0	2	220	350	0.5	0.1	57			2

4. Typical Characteristic



5. Dimension and Patterns (SOD-323)



UNIT	A	b_p	C	D	E	H_E	A_1	L_p
mm	1.20 0.90	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20

Notice

1. All product, product specifications and data are subject to change without notice to improve reliability, function or design or otherwise. The right to explain is owned by CCX electronics company.
2. Confirm that operation temperature is within the specified range described in the product specification.

Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
3. CCX shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.